



# AMDUA040N070RH

Single N-channel Trench MOSFET 40V 7.0mΩ 35A

## FEATURES

- Trench power MOSFET technology
- N-channel, normal level
- 100% Avalanche tested
- Maximum 175°C junction temperature
- AEC-Q101 qualified

## APPLICATIONS

- Motor inverter
- Switching applications

## KEY PERFORMANCE PARAMETERS

$V_{DS}$	40	V
$R_{DS(on), typ.}$	0.0061	$\Omega$
$I_D$	35	A
$Q_g$	24	nC
Junction temperature, $_{max}$	175	$^{\circ}C$

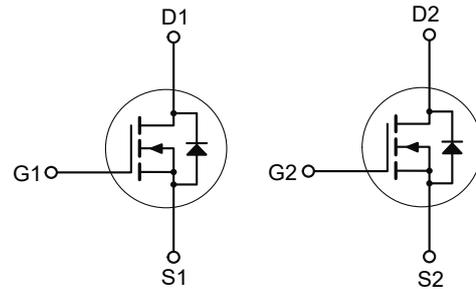


Top View

## PDFN56-DUAL



Bottom View



## ORDERING INFORMATION

Type / Ordering Code	Package	Marking	Packing	RoHS Status
AMDUA040N070RH	PDFN56-DUAL	040N070	Tape & Reel	Halogen Free

<http://www.magnachip.com/>

**ABSOLUTE MAXIMUM RATINGS**, at  $T_C = 25^\circ\text{C}$ , unless otherwise specified

PARAMETER		SYMBOL	RATING	UNIT
Drain-source Voltage		$V_{DS}$	40	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	
Drain current	$T_C=25^\circ\text{C}$ (Silicon Limited)	$I_D$	70	A
	$T_C=25^\circ\text{C}$ (Package Limited)		35	
	$T_C=100^\circ\text{C}$ (Silicon Limited)		49	
	$T_C=100^\circ\text{C}$ (Package Limited)		35	
<sup>1)</sup> Pulsed drain current	$T_C=25^\circ\text{C}$	$I_{DM}$	140	
Total power dissipation	$T_C=25^\circ\text{C}$	$P_{tot}$	60	W
	$T_C=100^\circ\text{C}$		30	
<sup>2)</sup> Avalanche energy, single pulse		$E_{AS}$	45	mJ
Operating and storage temperature		$T_J, T_{stg}$	- 55 ~ 175	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

PARAMETER		SYMBOL	RATING	UNIT
Thermal resistance, junction - case		$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
<sup>3)</sup> Thermal resistance, junction - ambient		$R_{\theta JA}$	50	

**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C)****STATIC CHARACTERISTICS**

PARAMETER	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	40	-	-	V	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA
Gate threshold voltage	V <sub>GS(th)</sub>	2.45	3.20	3.95	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =40 V, V <sub>GS</sub> =0 V
Gate-source leakage current	I <sub>GSS</sub>	-	-	± 100	nA	V <sub>GS</sub> =±20 V, V <sub>DS</sub> =0 V
Drain-source on-state resistance	R <sub>DS(on)</sub>	-	6.1	7.0	mΩ	V <sub>GS</sub> =10 V, I <sub>D</sub> =17.5 A
<sup>4)</sup> Gate resistance	R <sub>G</sub>	-	2.3	-	Ω	f=1 MHz
<sup>4)</sup> Transconductance	g <sub>fs</sub>	-	42	-	S	V <sub>DS</sub> =10 V, I <sub>D</sub> =17.5 A

**<sup>4)</sup> DYNAMIC CHARACTERISTICS**

PARAMETER	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Input capacitance	C <sub>iss</sub>	-	1658	2321	pF	V <sub>GS</sub> =0 V, V <sub>DS</sub> =20 V, f=1 MHz
Output capacitance	C <sub>oss</sub>	-	445	623		
Reverse transfer capacitance	C <sub>rss</sub>	-	41	66		
Turn-on delay time	t <sub>d(on)</sub>	-	17	-	ns	V <sub>DD</sub> =20 V, V <sub>GS</sub> =10 V, I <sub>D</sub> =17.5 A, R <sub>G,ext</sub> =3 Ω
Rise time	t <sub>r</sub>	-	11	-		
Turn-off delay time	t <sub>d(off)</sub>	-	27	-		
Fall time	t <sub>f</sub>	-	9	-		

**<sup>4)</sup> GATE CHARGE CHARACTERISTICS**

PARAMETER	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Gate to source charge	Q <sub>gs</sub>	-	9	13	nC	V <sub>DD</sub> =20 V, I <sub>D</sub> =17.5 A, V <sub>GS</sub> =0 to 10 V
Gate charge at threshold	Q <sub>gs(th)</sub>	-	5	-		
Gate to drain charge	Q <sub>gd</sub>	-	3	5		
Switching charge	Q <sub>sw</sub>	-	7	-		
Gate charge total	Q <sub>g</sub>	-	24	34		
Gate plateau voltage	V <sub>plateau</sub>	-	5.1	-	V	

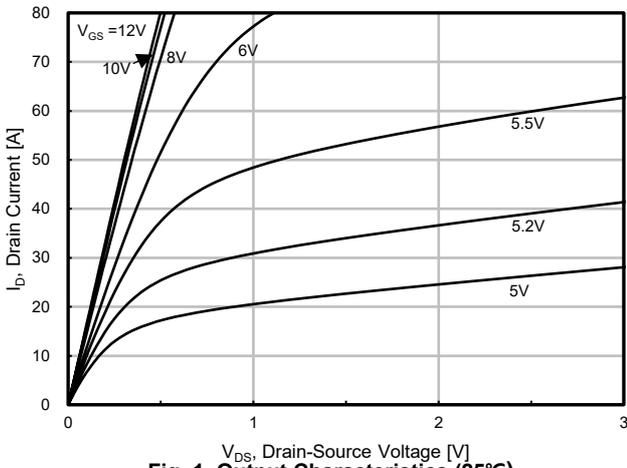
**SOURCE-DRAIN DIODE**

PARAMETER	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
<sup>4)</sup> Diode continuous forward current	I <sub>S</sub>	-	-	35	A	-
<sup>4)</sup> Diode pulse current	I <sub>S,pulse</sub>	-	-	140	A	pulsed; t <sub>p</sub> ≤ 10 μs
Diode forward voltage	V <sub>SD</sub>	-	0.9	1.2	V	V <sub>GS</sub> =0 V, I <sub>F</sub> =17.5 A
<sup>4)</sup> Reverse recovery time	t <sub>rr</sub>	-	35.9	-	ns	I <sub>F</sub> =17.5 A, di <sub>F</sub> /dt=100 A/μs
<sup>4)</sup> Reverse recovery charge	Q <sub>rr</sub>	-	19.4	-	nC	

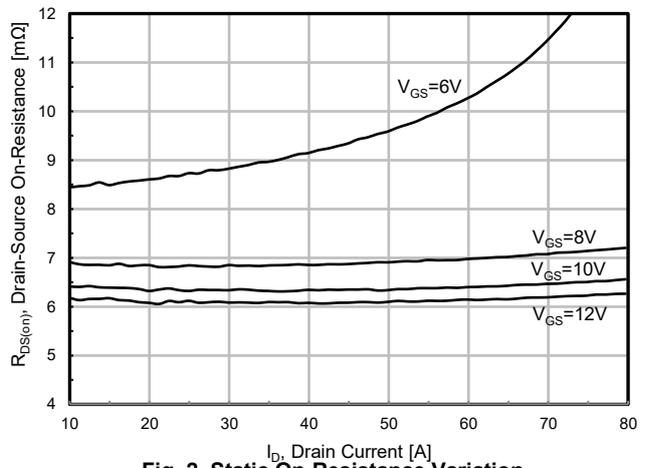
**Notes**

- Pulse width limited by T<sub>Jmax</sub>
- Starting T<sub>J</sub>=25°C, L=1mH, I<sub>AS</sub>=9.5A, V<sub>DD</sub>=36V, V<sub>GS</sub>=10V
- Surface mounted FR-4 board by JEDEC (jesd51-7)
- The parameter is not subject to production testing - guaranteed by design.

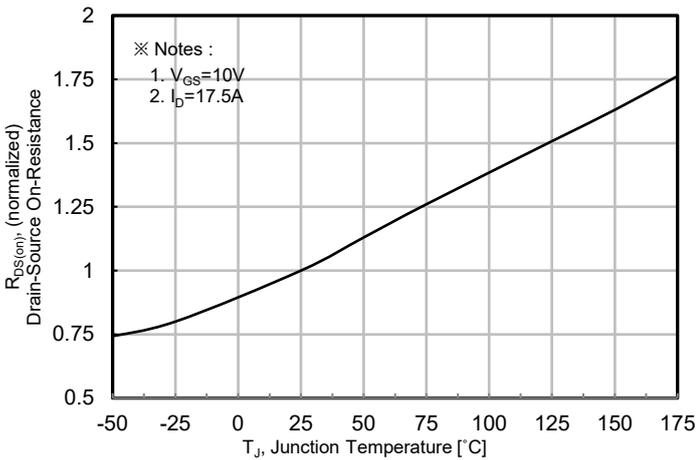
**ELECTRICAL CHARACTERISTICS DIAGRAMS (25 °C, unless otherwise noted)**



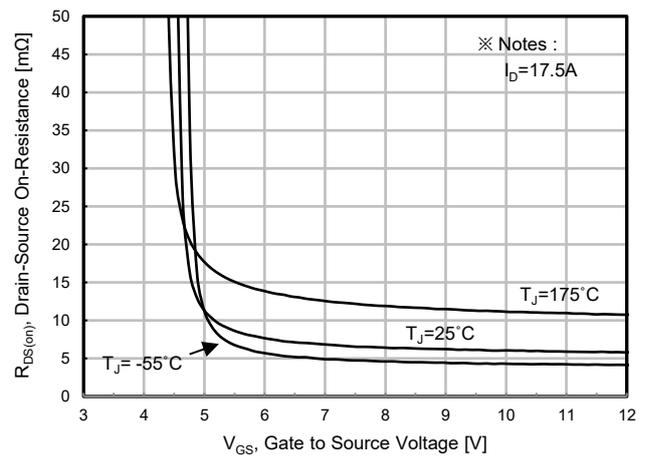
**Fig. 1. Output Characteristics (25°C)**



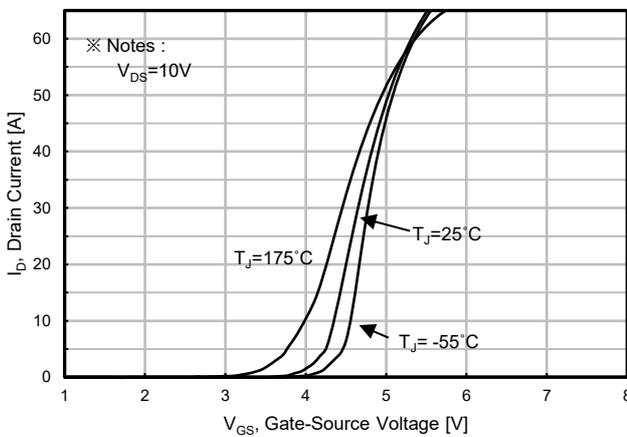
**Fig. 2. Static On-Resistance Variation**



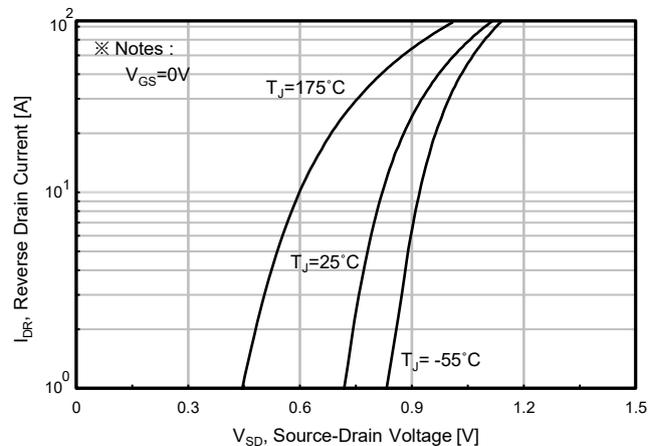
**Fig. 3. On-Resistance vs. Junction Temperature**



**Fig. 4. On-Resistance vs. Gate to source Voltage**

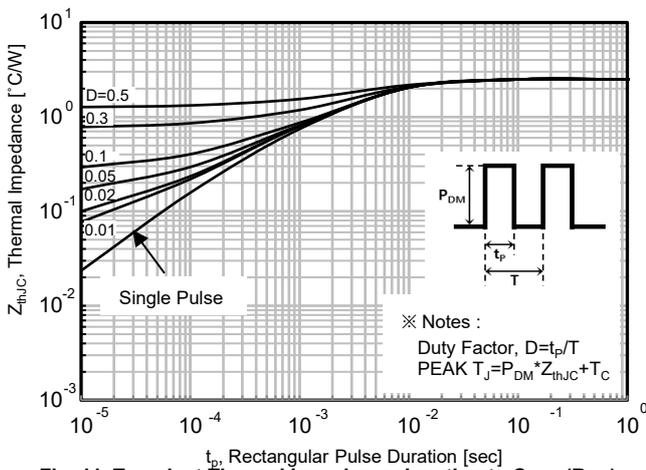
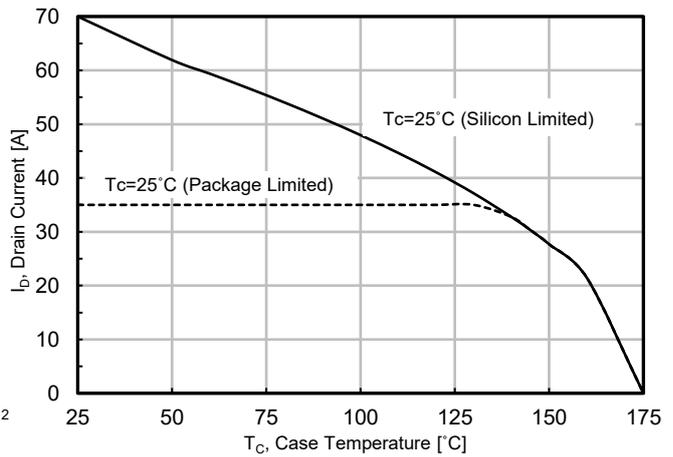
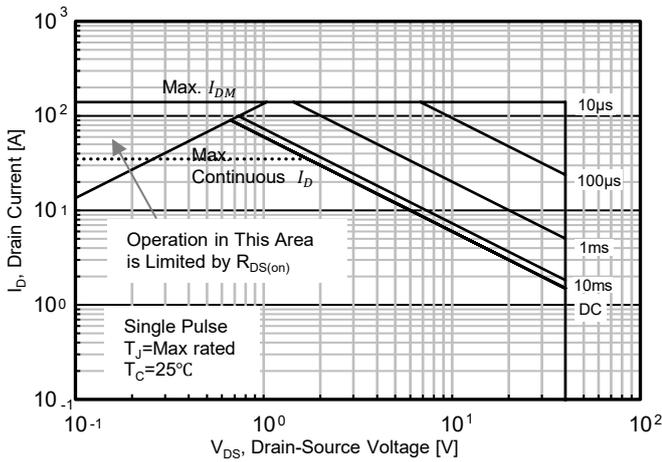
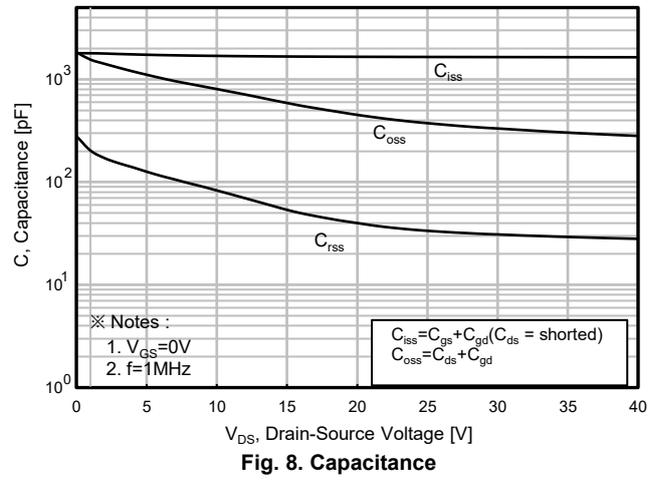
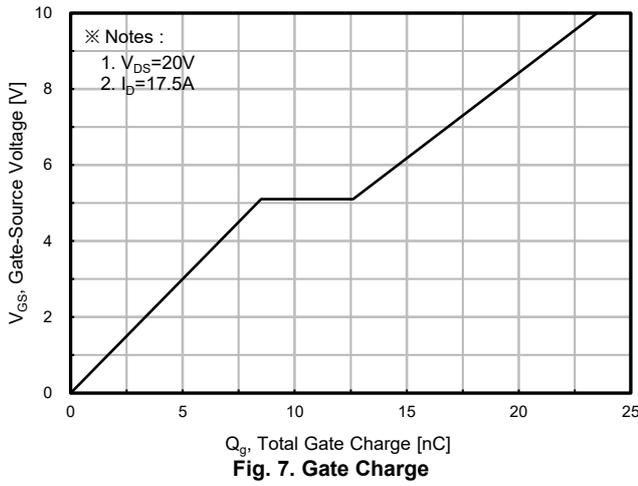


**Fig. 5. Transfer Characteristics**



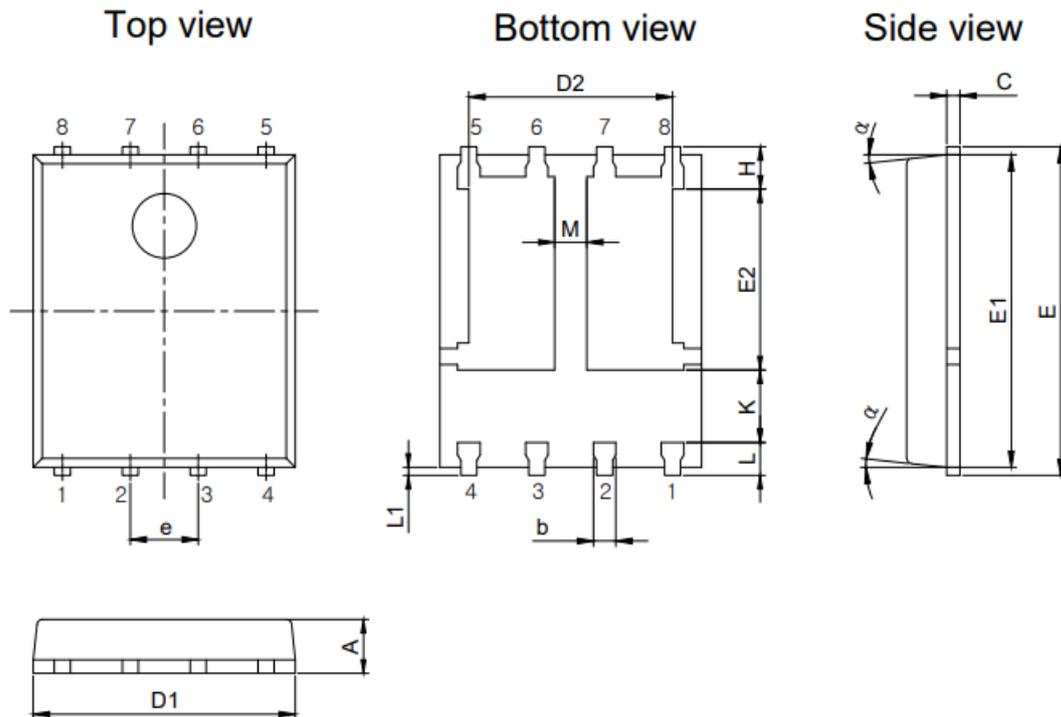
**Fig. 6. Body Diode Forward Voltage Variation with Source Current and Temperature**

**ELECTRICAL CHARACTERISTICS DIAGRAMS (25 °C, unless otherwise noted)**



# Package information

## PDFN56-DUAL



Symbol	Dimension (mm)		
	Min	Nom	Max
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	-	-
$\alpha$	0°	-	12°

### Notes

Package body size, length and width do not include mold flash, protrusions and gate burrs.

**DISCLAIMER :**

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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